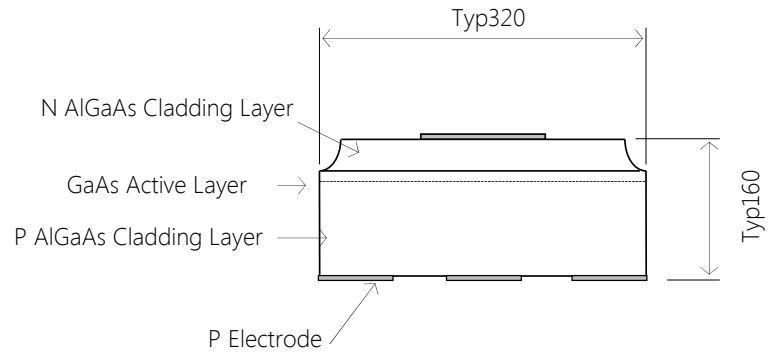
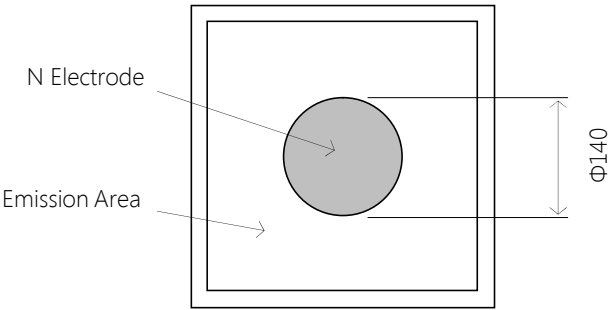


Radiation	Type	Electrodes
IR (870nm)	AlGaAs	(cathode) up



### Physical Characteristics

Material: AlGaAs      Bond Pad Size: 140um diameter  
 Junction Size: 320um x 320um      Anode Metalization: Gold Alloy  
 Thickness: 160um      Cathode Metalization: Gold Alloy

### Electrical Characteristics

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA	--	--	1.6	V
Reverse Voltage	V <sub>r</sub>	I <sub>r</sub> =10uA	5	--	--	V
radiant Power	Φ <sub>e</sub>	20 A	3.5			
Peak wavelength	ρ	20 A	850	870	900	nm
spectral width		20 A		45		nm
Rise Time	T <sub>r</sub>	I <sub>f</sub> p=100mA Tw=125ns, Duty=25%	--	20	--	ns
Fall Time	T <sub>f</sub>	I <sub>f</sub> p=100mA Tw=125ns, Duty=25%	--	20	--	ns
Peak Forward Voltage	V <sub>fm</sub>	I <sub>f</sub> p=400mA Tw=100us, Duty=10%	--	2.2	--	V

LED chip is mounted on T-1 gold leaded epoxy resin coated

### Absolute Maximum Ratings

Continuous Maximum Forward Current: 100 mA  
 Reverse Voltage: 10 V  
 Storage Temperature Range: 0 to 40 °C  
 Operating Temperature Range: 30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.